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			Application Number	TBD	
			Filing Date	11/01/01	
			First Named Inventor	Robert H. Havemann	
			Group Art Unit	TBD	
Examiner Name	TBD				
Sheet		of		Attorney Docket No.	TI-27506

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U.S. PATENT DOCUMENTS						
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881	CA	Zielinski et al, "Damascene Integration of Copper and Ultra-Low-k Xerogel for High Performance Interconnects," IEDM 97, pp. 936-938.			
	CB	Lee et al., "Application of HSQ (Hydrogen Silsesquioxane) Based SOG to Pre-Metal Dielectric Planarization in STC (Stacked Capacitor) DRAM," 1996 Symposium on VLSI Technology Digest of Technical Papers, pp. 112-113.			
	CC	List et al, "Integration of Ultra-Low-k Xerogel Gapfill Dielectric for High Performance Sub-0.18 μm Interconnects," 1997 Symposium on VLSI Technology Digest of Technical Papers, pp. 77-78.			
881	CD	Jeng, et al., "Process Integration and Manufacturability Issues for High Performance Multilevel Interconnect," Mat. Res. Soc. Symp. Proc., Vol. 337, pp. 25-31.			
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